
FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
(Rev. 5/92) 225 Franklin Street, Boston, MA 02110
Telephone: (617) 426-9180

PE CONTROL INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

MIT.9944 ATTORNEY DOCKET NO.

APPLICANT: McGill et al.

FILING DATE: August 1, 2003

10/632,442 SERIAL NO.

GROUP: Unknown

EXAMINER: Unknown

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M	"Metalorganic Vapor Phase Epitaxy Growth and Characterization of (Al _x Ga _{1-x}) _{0.5} In _{0.5} P/Ga _{0.5} In _{0.5} P(x=0.4, 0.7, and 1.0) Quantum Wells on 15° -Off-(100) GaAs Substrates at High Growth Rate" Jou et al. <i>Jpn. Journal of Applied Physics</i> . October 1993. Vol. 32, No. 10.									
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FILING DATE: Herewith 08/01/03

Unknown 10/632,442 SERIAL NO.

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1//	N	"High-Efficiency InGaP Light-Emitting Diodes on GaP Substrates," Stinson et al. Applied Physics Letters. May 1991. Vol. 58, No. 18.
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h	АМ	"Yellow-Green Emission for ETS-LEDs and lasers based on a strained-InGaP quantum well heterostructure grown on a transparent, compositionally graded AlinGaP buffer," McGill et al. Mat. Res. Symp. Proc. 2003. Vol. 744
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Initial if citati n c nsidered, wh ther rn t citati n is in c nf rmance with MPEP 609; draw line thr ugh citation if n t in c nf rmance and n t c nsidered. Include c py f this f rm with next c mmunication to applicant.

(Rev. 5/92)	-1449 SAMUELS, GAUTHIER & STEVENS LLP 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180				ATTORNEY DOCKET NO. APPLICANT: McGill et al.			SERIAL NO. GROUP: Unknown		
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B	AJ	"Evolution of m metalorganic va Technol. B. Jul/	por phase epitax	cy: er	location dynamics in ngineering device-qu	In _a Ga _{1-a} P vality subst	graded Brater	uffers ials,"	grown on GaP by Kim et al. J. Vac. Sci.	
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